

In the Claims:

Please amend claims 1, 2, 4, 6, 7 and 10 as set forth below in the "Listing of Claims".

Please cancel claims 11-13.

LISTING OF CLAIMS

Claim 1 (Currently Amended): A film forming method comprising:

supplying simultaneously a vapor of a hafnium organic compound and a silane-series gas into a reaction vessel to react the reacting a hafnium organic compound and a the silane-series gas with each other in a the reaction vessel, thereby depositing a hafnium silicate film on a substrate by a chemical vapor deposition process.

Claim 2 (Currently Amended): The film forming method according to claim 1, wherein a heated atmosphere is established in an interior of the reaction vessel[[,]] when depositing the hafnium silicate film and the hafnium organic compound is supplied into the reaetion vessel in a vapor state.

Claim 3 (Previously Presented): The film forming method according to claim 1, wherein the silane-series gas comprises monosilane gas and/or disilane gas.

Claim 4 (Currently Amended): A film forming method comprising:

depositing a hafnium ~~compound~~ silicate film ~~containing hafnium and oxygen~~ on a substrate; and
annealing the hafnium ~~compound~~ silicate film, obtained by the depositing, in an atmosphere of a compound gas of nitrogen and hydrogen.

Claim 5 (Original): The film forming method according to claim 4, wherein the compound gas of nitrogen and hydrogen is ammonia gas.

Claim 6 (Currently Amended): The film forming method according to claim 4 further comprising:

depositing a silicon nitride film directly on the hafnium silicate film after the annealing of the hafnium compound silicate film.

Claim 7 (Currently Amended): The film forming method according to claim 4, wherein the hafnium compound film is a hafnium silicate film deposited by reacting a hafnium organic compound and a silane-series gas step of depositing the silicon hafnium film includes a step of supplying simultaneously a vapor of a hafnium organic compound and a silane-series gas into a reaction vessel to react the hafnium organic compound and the silane-series gas with each other in the reaction vessel, thereby depositing the hafnium silicate film on the substrate by a chemical vapor deposition.

Claim 8 (Withdrawn): A film forming apparatus comprising:

a reaction vessel into which a substrate is loaded;
a heating mechanism that heats an atmosphere in the reaction vessel;
a first gas-supplying means for supplying a vapor of a hafnium organic compound into the reaction vessel;
a second gas-supplying means for supplying a silane-series gas into the reaction vessel; and
a controller that controls the heating mechanism and the first and second gas-supplying means to deposit a hafnium silicate film on a substrate by reacting the hafnium organic compound and the silane-series gas in the reaction vessel.

Claim 9 (Previously Presented): The film forming method according to claim 2, wherein the silane-series gas comprises monosilane gas and/or disilane gas.

Claim 10 (Currently Amended): The film forming method according to claim 5 further comprising: depositing a silicon nitride film directly on the hafnium silicate film after the annealing of the hafnium ~~compound~~ silicate film.

Claims 11-13 (Canceled)